

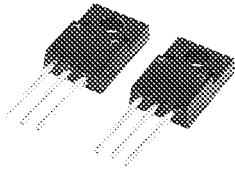
**PRELIMINARY**  
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MITSUBISHI Pch POWER MOSFET

# FX6KMJ-2

HIGH-SPEED SWITCHING USE

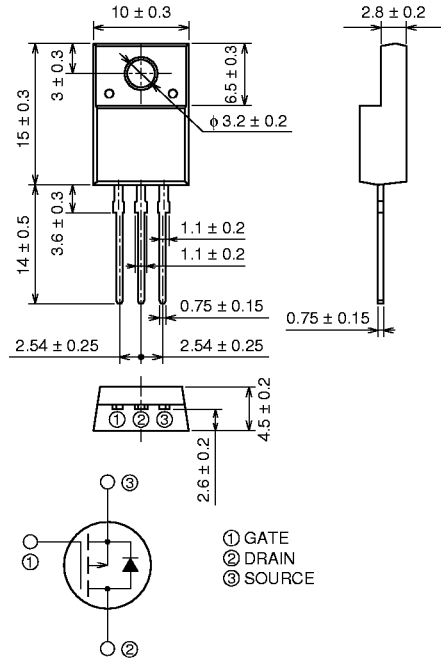
## FX6KMJ-2



- 4V DRIVE
- $V_{DSS}$  ..... -100V
- $r_{DS(ON)}$  (MAX) ..... 0.58Ω
- $I_D$  ..... -6A
- Integrated Fast Recovery Diode (TYP.) ..... 80ns
- $V_{iso}$  ..... 2000V

## OUTLINE DRAWING

Dimensions in mm



TO-220FN

## APPLICATION

Motor control, Lamp control, Solenoid control  
 DC-DC converter, etc.

## MAXIMUM RATINGS (T<sub>c</sub> = 25 °C)

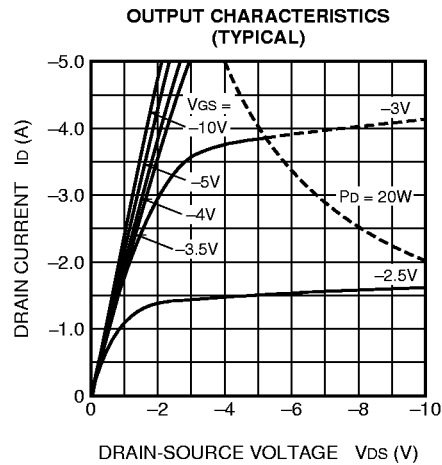
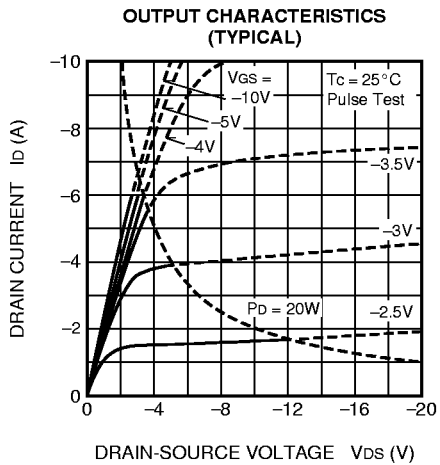
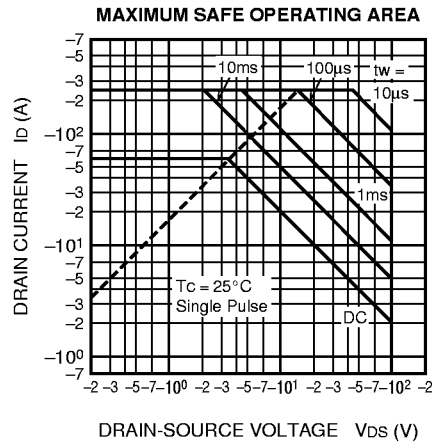
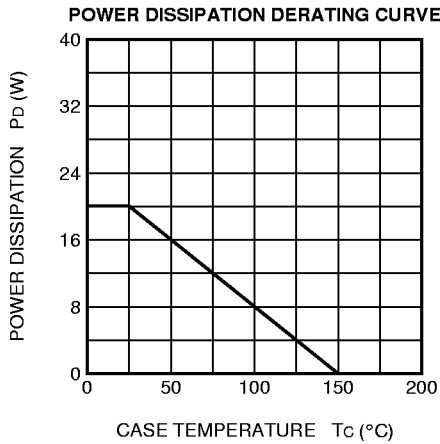
Symbol	Parameter	Conditions	Ratings	Unit
$V_{DSS}$	Drain-source voltage	$V_{GS} = 0V$	-100	V
$V_{GSS}$	Gate-source voltage	$V_{DS} = 0V$	±20	V
$I_D$	Drain current		-6	A
$I_{DM}$	Drain current (Pulsed)		-24	A
$I_{DA}$	Avalanche drain current (Pulsed)	$L = 100\mu H$	-6	A
$I_S$	Source current		-6	A
$I_{SM}$	Source current (Pulsed)		-24	A
$P_D$	Maximum power dissipation		20	W
$T_{ch}$	Channel temperature		-55 ~ +150	°C
$T_{stg}$	Storage temperature		-55 ~ +150	°C
$V_{iso}$	Isolation voltage	AC for 1 minute, Terminal to case	2000	V
—	Weight	Typical value	2.0	g

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**ELECTRICAL CHARACTERISTICS** (Tch = 25°C)

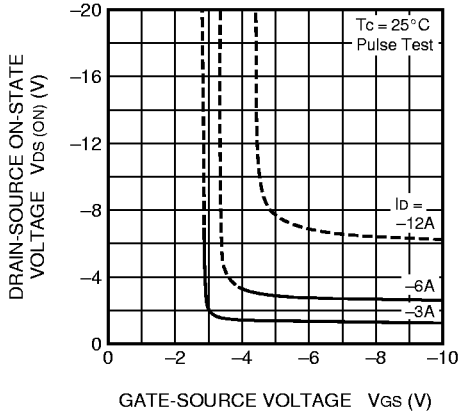
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V(BR)DSS	Drain-source breakdown voltage	ID = -1mA, VGS = 0V	-100	—	—	V
IGSS	Gate-source leakage current	VGS = ±20V, VDS = 0V	—	—	±0.1	μA
IDSS	Drain-source leakage current	VDS = -100V, VGS = 0V	—	—	-0.1	mA
VGS(th)	Gate-source threshold voltage	ID = -1mA, VDS = -10V	-1.0	-1.5	-2.0	V
rDS(ON)	Drain-source on-state resistance	ID = -3A, VGS = -10V	—	0.46	0.58	Ω
rDS(ON)	Drain-source on-state resistance	ID = -3A, VGS = -4V	—	0.55	0.72	Ω
VDS(ON)	Drain-source on-state voltage	ID = -3A, VGS = -10V	—	-1.38	-1.74	V
yfs	Forward transfer admittance	ID = -3A, VDS = -5V	—	4.7	—	S
Ciss	Input capacitance	VDS = -10V, VGS = 0V, f = 1MHz	—	1110	—	pF
Coss	Output capacitance		—	108	—	pF
Crss	Reverse transfer capacitance		—	44	—	pF
td(on)	Turn-on delay time	VDD = -50V, ID = -3A, VGS = -10V, RGEN = RGS = 50Ω	—	9	—	ns
tr	Rise time		—	8	—	ns
td(off)	Turn-off delay time		—	72	—	ns
tf	Fall time		—	33	—	ns
VSD	Source-drain voltage		IS = -3A, VGS = 0V	—	-1.0	-1.5
Rth(ch-c)	Thermal resistance	Channel to case	—	—	6.25	°C/W
trr	Reverse recovery time	IS = -6A, dis/dt = 100A/μs	—	80	—	ns

**PERFORMANCE CURVES**

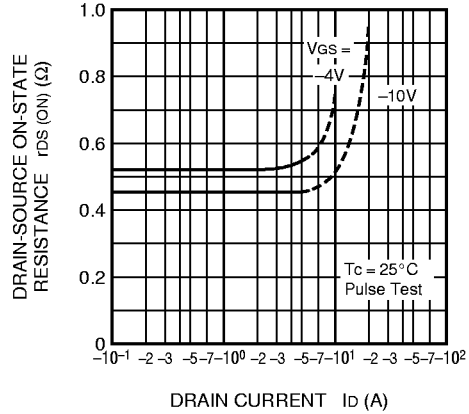


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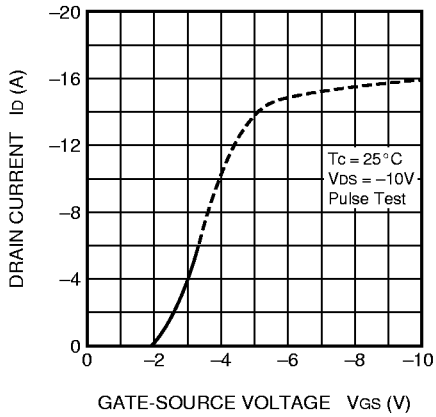
**ON-STATE VOLTAGE VS. GATE-SOURCE VOLTAGE (TYPICAL)**



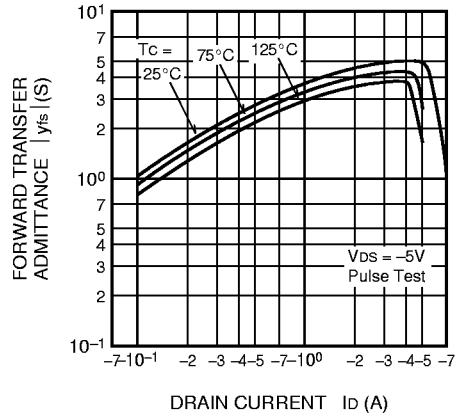
**ON-STATE RESISTANCE VS. DRAIN CURRENT (TYPICAL)**



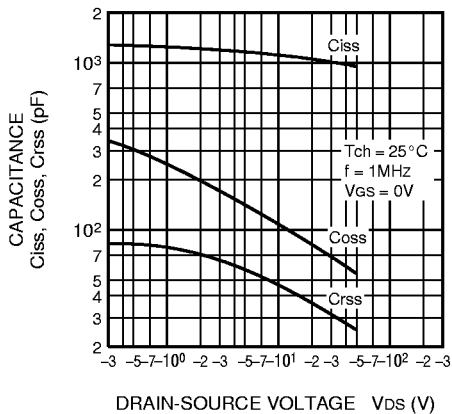
**TRANSFER CHARACTERISTICS (TYPICAL)**



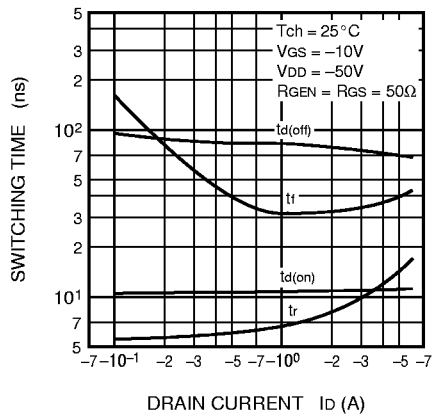
**FORWARD TRANSFER ADMITTANCE VS. DRAIN CURRENT (TYPICAL)**



**CAPACITANCE VS. DRAIN-SOURCE VOLTAGE (TYPICAL)**

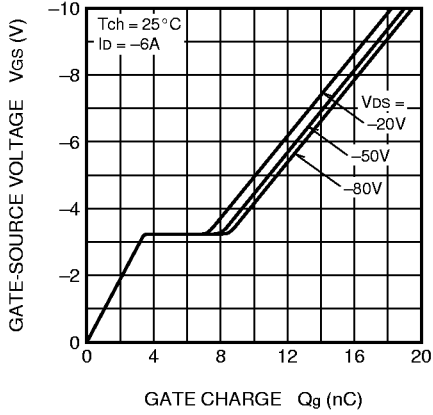


**SWITCHING CHARACTERISTICS (TYPICAL)**

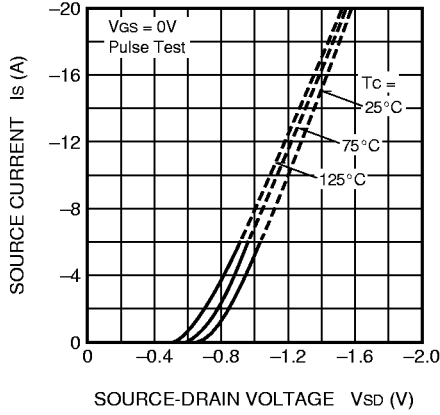


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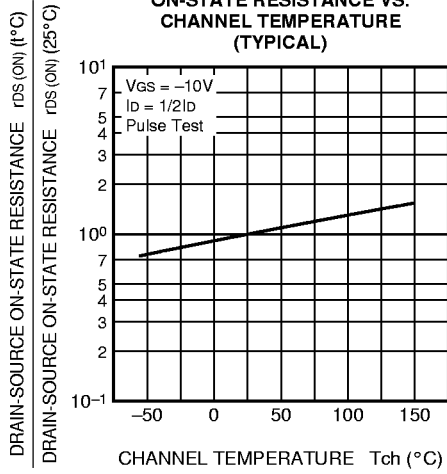
**GATE-SOURCE VOLTAGE VS. GATE CHARGE (TYPICAL)**



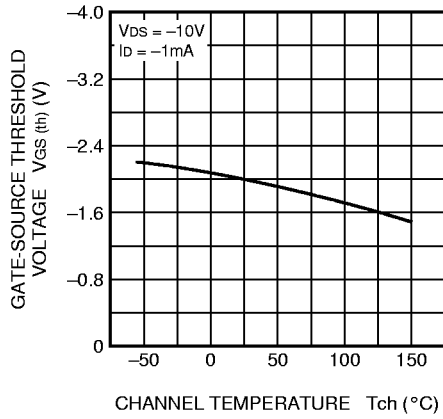
**SOURCE-DRAIN DIODE FORWARD CHARACTERISTICS (TYPICAL)**



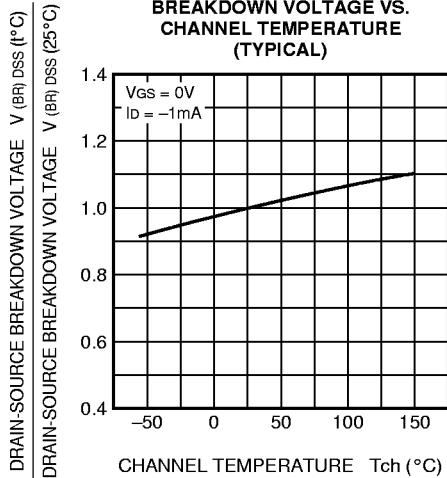
**ON-STATE RESISTANCE VS. CHANNEL TEMPERATURE (TYPICAL)**



**THRESHOLD VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)**



**BREAKDOWN VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)**



**TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS**

